

a' active layer 53 is provided on the n-type semiconductor layer 51. A p-type semiconductor layer 54 is provided on the active layer 53. A contact layer 55 is provided on the p-type semiconductor layer 54. A p electrode 56, which is a transparent electrode, is provided on the contact layer 55. A pad 57 is provided on the p electrode 56. A current is fed to the pad 57 from an external power source (not shown) through a wire 58.

In the Claims:

- 1 1. (amended) A semiconductor light-emitting device comprising:
2 a substrate and an n-type lower electrode provided on
3 a back surface of said substrate,
4 a light-emitting layer provided on said substrate;
5 a p-type semiconductor layer provided on said
6 light-emitting layer;
7 an Au thin film provided on said p-type semiconductor
8 layer and having a thickness of 1 nm to 3 nm; and
9 an n-type transparent conductive film provided on said
10 Au thin film, with said Au thin film between said p-type
11 semiconductor layer and said n-type transparent conductive
12 film.

Please cancel claims 2 and 3.